Operational Amplifiers, Low Noise, Dual and Quad

The MC33078/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input voltage noise with high gain bandwidth product and slew rate. The all NPN output stage exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open loop high frequency output impedance and symmetrical source and sink AC frequency performance.

The MC33078/9 family offers both dual and quad amplifier versions and is available in the plastic DIP and SOIC packages (P and D suffixes).

Features

• Dual Supply Operation: $\pm 5.0 \text{ V}$ to $\pm 18 \text{ V}$

• Low Voltage Noise: 4.5 nV/√Hz

• Low Input Offset Voltage: 0.15 mV

• Low T.C. of Input Offset Voltage: 2.0 μV/°C

• Low Total Harmonic Distortion: 0.002%

• High Gain Bandwidth Product: 16 MHz

• High Slew Rate: 7.0 V/µs

• High Open Loop AC Gain: 800 @ 20 kHz

• Excellent Frequency Stability

• Large Output Voltage Swing: +14.1 V/ -14.6 V

• ESD Diodes Provided on the Inputs

• NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

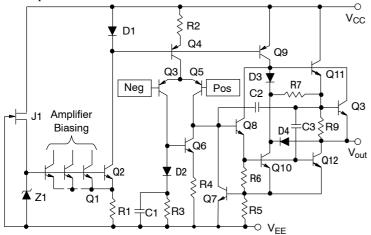


Figure 1. Representative Schematic Diagram (Each Amplifier)



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MARKING DIAGRAMS

DUAL



PDIP-8 **P SUFFIX CASE 626**





SOIC-8 **D SUFFIX CASE 751**



QUAD

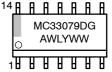


PDIP-14 **P SUFFIX CASE 646**





SOIC-14 **D SUFFIX** CASE 751A



= Assembly Location

= Wafer Lot = Year

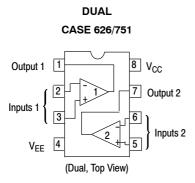
WW. W = Work Week

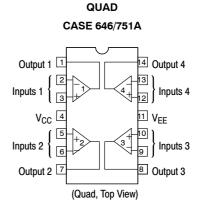
= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

PIN CONNECTIONS





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage (V _{CC} to V _{EE)}	Vs	+36	V
Input Differential Voltage Range	V _{IDR}	Note 1	V
Input Voltage Range	V _{IR}	Note 1	V
Output Short Circuit Duration (Note 2)	t _{SC}	Indefinite	sec
Maximum Junction Temperature	TJ	+150	°C
Storage Temperature	T _{stg}	-60 to +150	°C
ESD Protection at any Pin MC33078/NCV33078 - Human Body Model - Machine Model MC33079/NCV33079 - Human Body Model - Human Body Model - Machine Model	V _{esd}	600 200 550 150	V
Maximum Power Dissipation	P _D	Note 2	mW
Operating Temperature Range	T _A	-40 to +85	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Either or both input voltages must not exceed the magnitude of V_{CC} or V_{EE} .
- 2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (see Figure 2).

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage ($R_S = 10~\Omega,~V_{CM} = 0~V,~V_O = 0~V$) (MC33078) $T_A = +25^{\circ}C$ $T_A = -40^{\circ}~to~+85^{\circ}C$ (MC33079) $T_A = +25^{\circ}C$ $T_A = -40^{\circ}~to~+85^{\circ}C$	V _{IO}	- - -	0.15 - 0.15 -	2.0 3.0 2.5 3.5	mV
Average Temperature Coefficient of Input Offset Voltage R_S = 10 Ω , V_{CM} = 0 V, V_O = 0 V, T_A = T_{low} to T_{high}	$\Delta V_{IO}/\Delta T$	-	2.0	-	μV/°C
Input Bias Current (V_{CM} = 0 V, V_{O} = 0 V) T_{A} = +25°C T_{A} = -40° to +85°C	I _{IB}	- -	300 -	750 800	nA
Input Offset Current ($V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$) $T_A = +25^{\circ}\text{C}$ $T_A = -40^{\circ} \text{ to } +85^{\circ}\text{C}$	l _{IO}	- -	25 -	150 175	nA
Common Mode Input Voltage Range ($\Delta V_{IO} = 5.0$ mV, $V_{O} = 0$ V)	V _{ICR}	±13	±14	-	V
Large Signal Voltage Gain (V $_O$ = ±10 V, R $_L$ = 2.0 k $\Omega)$ T $_A$ = +25 $^{\circ}C$ T $_A$ = -40 $^{\circ}$ to +85 $^{\circ}C$	Avol	90 85	110 -	- -	dB
Output Voltage Swing (V_{ID} = \pm 1.0V) R_L = 600 Ω R_L = 600 Ω R_L = 2.0 k Ω R_L = 2.0 k Ω R_L = 10 k Ω R_L = 10 k Ω	V _O + V _O - V _O + V _O - V _O + V _O -	- +13.2 - +13.5	+10.7 -11.9 +13.8 -13.7 +14.1 -14.6	- - - -13.2 - -14	V
Common Mode Rejection (V _{in} = ±13V)	CMR	80	100	-	dB
Power Supply Rejection (Note 3) $V_{CC}/V_{EE} = +15 \text{ V}/ -15 \text{ V}$ to $+5.0 \text{ V}/ -5.0 \text{ V}$	PSR	80	105	-	dB
Output Short Circuit Current (V _{ID} = 1.0 V, Output to Ground) Source Sink	I _{SC}	+15 -20	+29 -37	- -	mA
Power Supply Current (V_O = 0 V, All Amplifiers) (MC33078) T_A = +25°C T_A = -40° to +85°C (MC33079) T_A = +25°C T_A = -40° to +85°C	Ι _D	- - - -	4.1 - 8.4 -	5.0 5.5 10 11	mA

^{3.} Measured with V_{CC} and V_{EE} differentially varied simultaneously.

AC ELECTRICAL CHARACTERISTICS ($V_{CC} = +15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $T_A = 25^{\circ}\text{C}$, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Slew Rate (V _{in} = –10 V to +10 V, R _L = 2.0 k Ω , C _L = 100 pF A _V = +1.0)	SR	5.0	7.0	-	V/μs
Gain Bandwidth Product (f = 100 kHz)	GBW	10	16	-	MHz
Unity Gain Bandwidth (Open Loop)	BW	-	9.0	-	MHz
Gain Margin (R_L = 2.0 k Ω) C_L = 0 pF C_L = 100 pF	A _m	_ _	-11 -6.0	- -	dB
Phase Margin (R_L = 2.0 k Ω) C_L = 0 pF C_L = 100 pF	Фт	_ _	55 40	- -	Deg
Channel Separation (f = 20 Hz to 20 kHz)	CS	-	-120	-	dB
Power Bandwidth ($V_O = 27 V_{pp}$, $R_L = 2.0 k\Omega$, THD $\pm 1.0\%$)	BW _p	-	120	-	kHz
Total Harmonic Distortion (R _L = 2.0 k Ω , f = 20 Hz to 20 kHz, V _O = 3.0 V _{rms} , A _V = +1.0)	THD	-	0.002	-	%
Open Loop Output Impedance (V _O = 0 V, f = 9.0 MHz)	Z _O	-	37	-	Ω
Differential Input Resistance (V _{CM = 0 V)}	R _{in}	_	175	-	kΩ
Differential Input Capacitance (V _{CM = 0 V)}	C _{in}	_	12	-	pF
Equivalent Input Noise Voltage ($R_S = 100 \Omega$, $f = 1.0 \text{ kHz}$)	e _n	_	4.5	-	nV/√Hz
Equivalent Input Noise Current (f = 1.0 kHz)	i _n	_	0.5	_	Hz√pA/

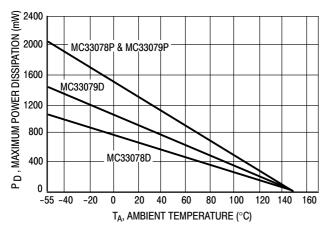


Figure 2. Maximum Power Dissipation versus Temperature

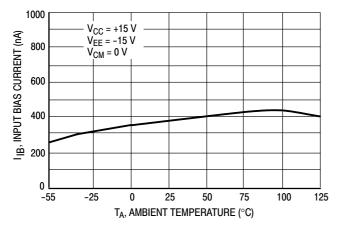


Figure 4. Input Bias Current versus Temperature

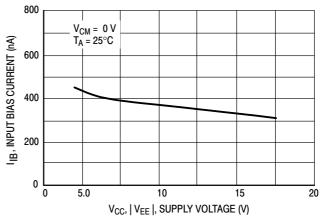


Figure 3. Input Bias Current versus Supply Voltage

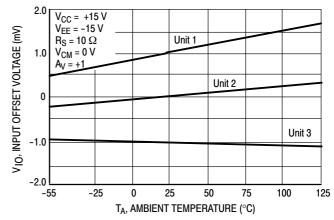


Figure 5. Input Offset Voltage versus Temperature

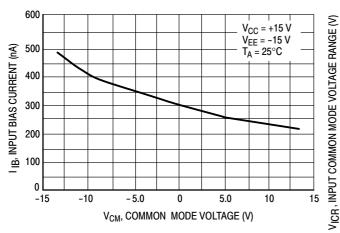


Figure 6. Input Bias Current versus Common Mode Voltage

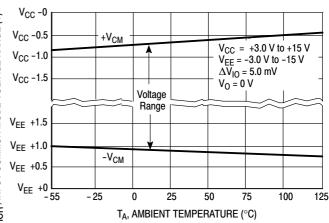


Figure 7. Input Common Mode Voltage Range versus Temperature

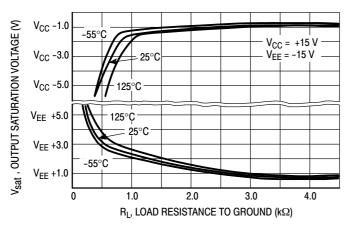


Figure 8. Output Saturation Voltage versus Load Resistance to Ground

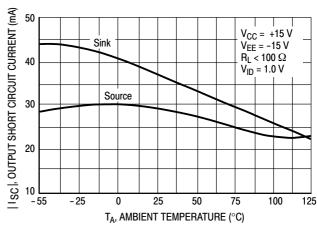


Figure 9. Output Short Circuit Current versus Temperature

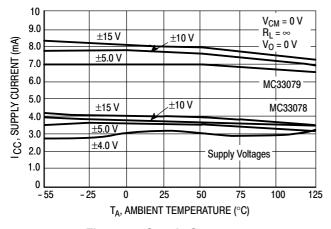


Figure 10. Supply Current versus Temperature

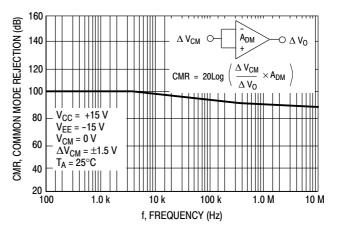


Figure 11. Common Mode Rejection versus Frequency

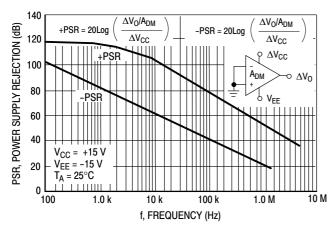


Figure 12. Power Supply Rejection versus Frequency

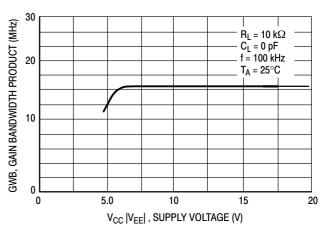


Figure 13. Gain Bandwidth Product versus Supply Voltage

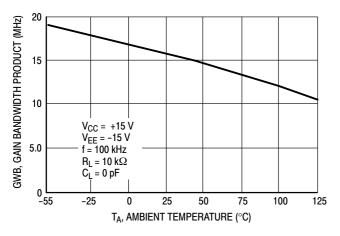


Figure 14. Gain Bandwidth Product versus Temperature

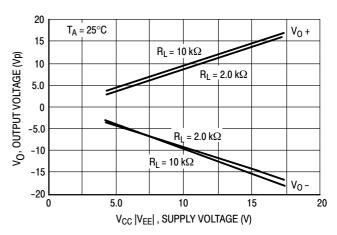


Figure 15. Maximum Output Voltage versus Supply Voltage

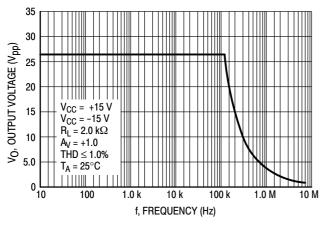


Figure 16. Output Voltage versus Frequency

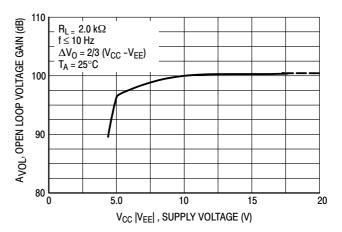


Figure 17. Open Loop Voltage Gain versus Supply Voltage

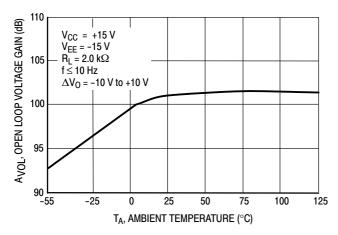


Figure 18. Open Loop Voltage Gain versus Temperature

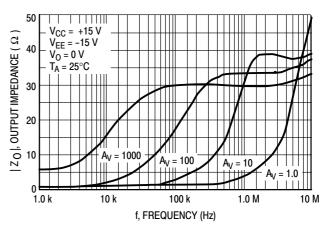


Figure 19. Output Impedance versus Frequency

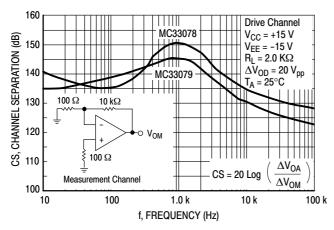


Figure 20. Channel Separation versus Frequency

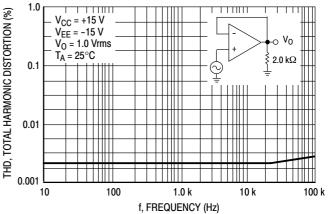


Figure 21. Total Harmonic Distortion versus Frequency

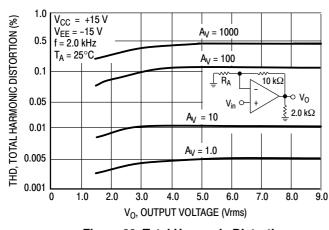


Figure 22. Total Harmonic Distortion versus Output Voltage

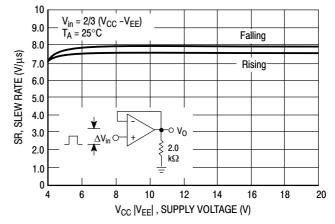


Figure 23. Slew Rate versus Supply Voltage

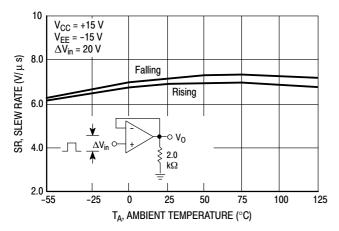


Figure 24. Slew Rate versus Temperature

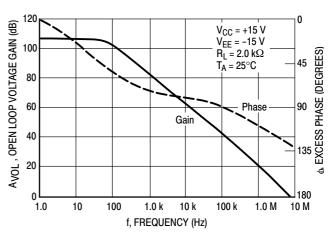


Figure 25. Voltage Gain and Phase versus Frequency

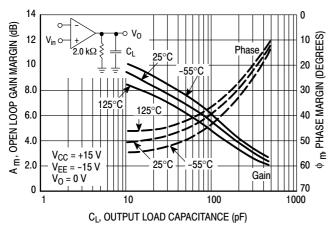


Figure 26. Open Loop Gain Margin and Phase Margin versus Load Capacitance

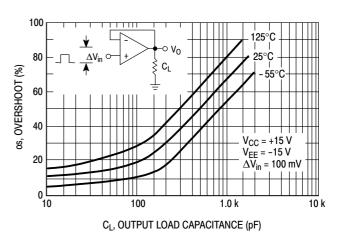


Figure 27. Overshoot versus Output Load Capacitance

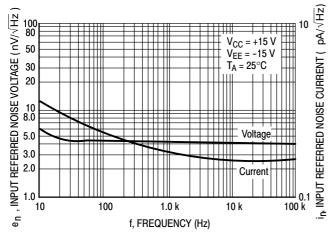


Figure 28. Input Referred Noise Voltage and Current versus Frequency

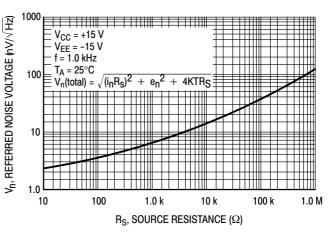


Figure 29. Total Input Referred Noise Voltage versus Source Resistance

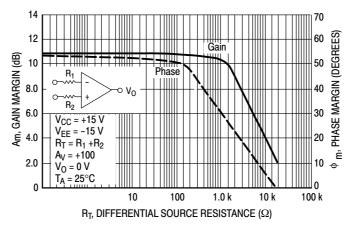


Figure 30. Phase Margin and Gain Margin versus Differential Source Resistance

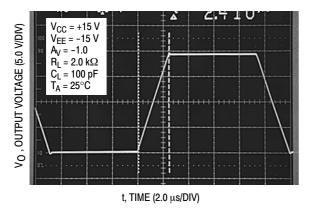


Figure 31. Inverting Amplifier Slew Rate

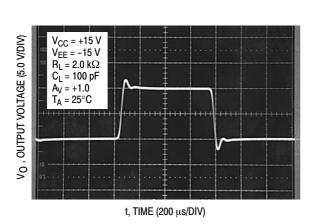


Figure 33. Non-inverting Amplifier Overshoot

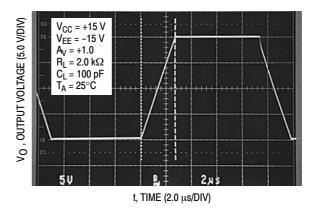


Figure 32. Non-inverting Amplifier Slew Rate

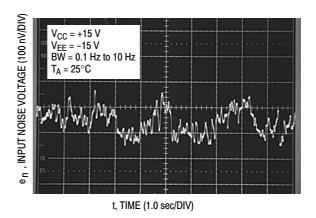
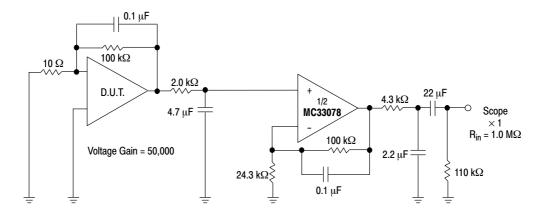


Figure 34. Low Frequency Noise Voltage versus Time



Note: All capacitors are non-polarized.

Figure 35. Voltage Noise Test Circuit (0.1 Hz to 10 ${\rm Hz}_{\rm p-p}$)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC33078DG		98 Units / Rail
MC33078DR2G	SOIC-8 (Pb-Free)	0500 / Tono 9 Dool
NCV33078DR2G*	, ,	2500 / Tape & Reel
MC33078P	PDIP-8	
MC33078PG	PDIP-8 (Pb-Free)	50 Units / Rail
MC33079DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC33079DR2G	SOIC-14	2500 / Tape & Reel
NCV33079DR2G*	(Pb-Free)	2500 / Tape & Neel
MC33079P	PDIP-14	
MC33079PG	PDIP-14 (Pb-Free)	25 Units / Rail

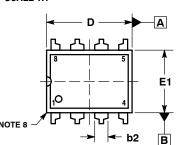
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NCV devices are qualified for automotive use.

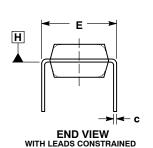


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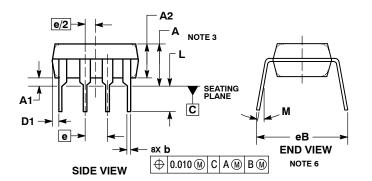
DATE 22 APR 2015



TOP VIEW



NOTE 5



STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN

5. GROUND 6. OUTPUT

7. AUXILIARY 8. V_{CC}

NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
 DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- 6. DIMENSION 6B IS MEASURED AT THE LEAD TIPS WITH THE
- LEADS UNCONSTRAINED.

 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	0.060 TYP		TYP
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
Е	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54	BSC
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

GENERIC MARKING DIAGRAM*



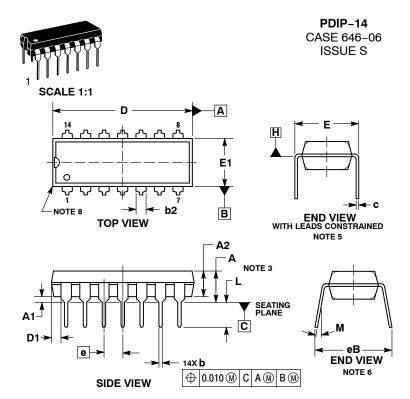
XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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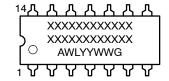
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: INCHES.
 3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
 4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
- NOT TO EXCEED 0.10 INCH.
 DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- DIMENSION 6B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.

 PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE
- CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
M		10°		10°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLES ON PAGE 2

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PDIP-14 CASE 646-06 ISSUE S

DATE 22 APR 2015

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. DRAIN 2. SOURCE 3. GATE 4. NO CONNECTION 5. GATE 6. SOURCE 7. DRAIN 8. DRAIN 9. SOURCE 10. GATE 11. NO CONNECTION 12. GATE 13. SOURCE 14. DRAIN
STYLE 5: PIN 1. GATE 2. DRAIN 3. SOURCE 4. NO CONNECTION 5. SOURCE 6. DRAIN 7. GATE 8. GATE 9. DRAIN 10. SOURCE 11. NO CONNECTION 12. SOURCE 13. DRAIN 14. GATE	STYLE 6: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 7: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 8: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 9: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE	STYLE 10: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 12: PIN 1. COMMON CATHODE 2. COMMON ANODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. COMMON ANODE 7. COMMON CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. ANODE/CATHODE 14. ANODE/CATHODE 14. ANODE/CATHODE

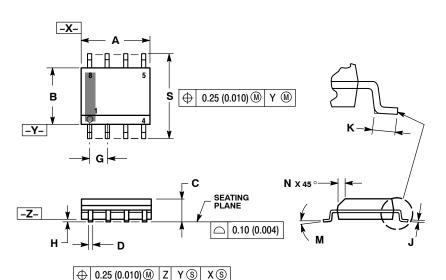
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SOIC-8 NB CASE 751-07 **ISSUE AK**

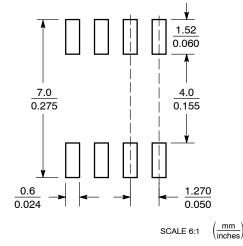
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

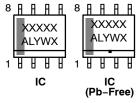
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
7	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package

XXXXXX = Specific Device Code = Assembly Location Α = Year ww = Work Week = Pb-Free Package

XXXXXX

AYWW

Discrete

H \mathbb{H} AYWW

Discrete (Pb-Free)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	7. BASE, #1 8. EMITTER, #1 STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
5. RXE 6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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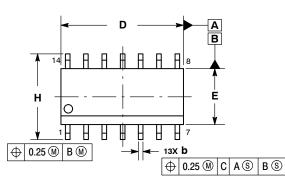
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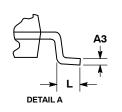


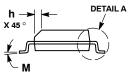
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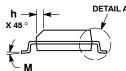
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





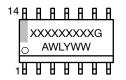




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION
- SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



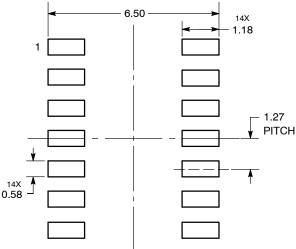
XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*

C SEATING PLANE



DIMENSIONS: MILLIMETERS

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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